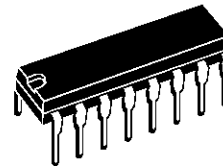


DUAL POWER AMPLIFIER

- SUPPLY VOLTAGE DOWN TO 3 V
- HIGH SVR
- LOW CROSSOVER DISTORTION
- LOW QUIESCENT CURRENT
- BRIDGE OR STEREO CONFIGURATION

DESCRIPTION

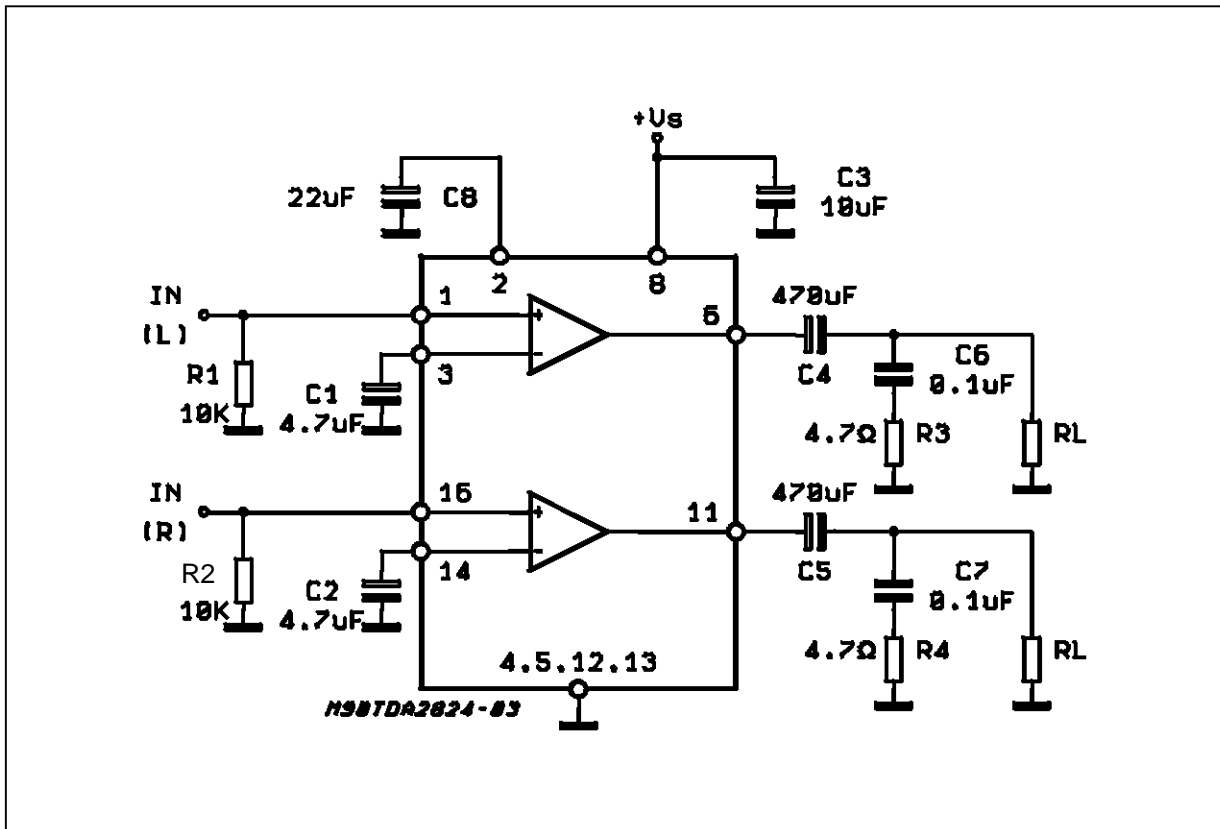
The TDA2824 is a monolithic integrated circuit in 12+2+2 powerdip, intended for use as dual audio power amplifier in portable radios and TV sets.



Powerdip (12+2+2)

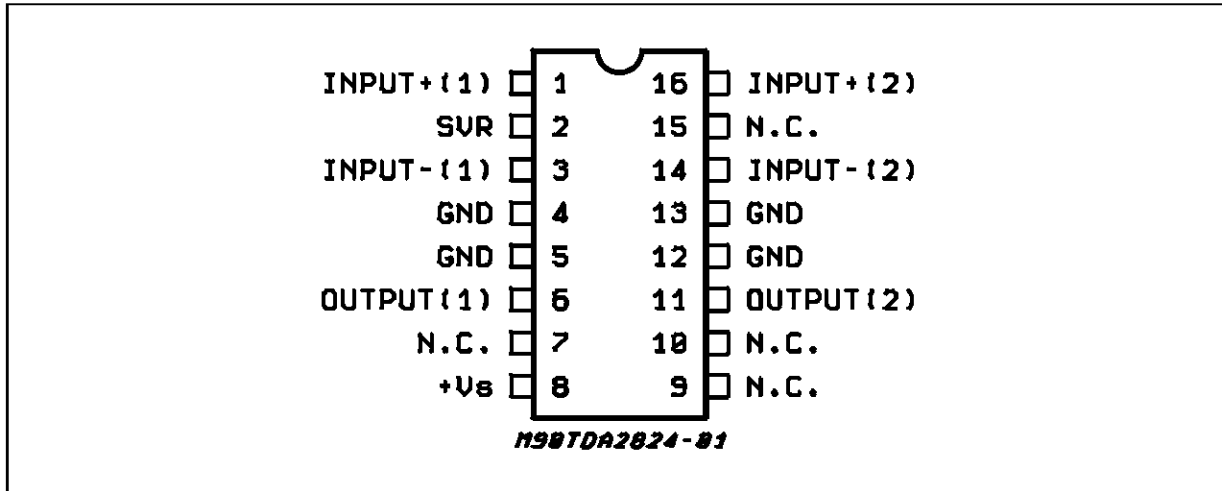
ORDERING NUMBER : TDA2824

TYPICAL APPLICATION CIRCUIT (Stereo)

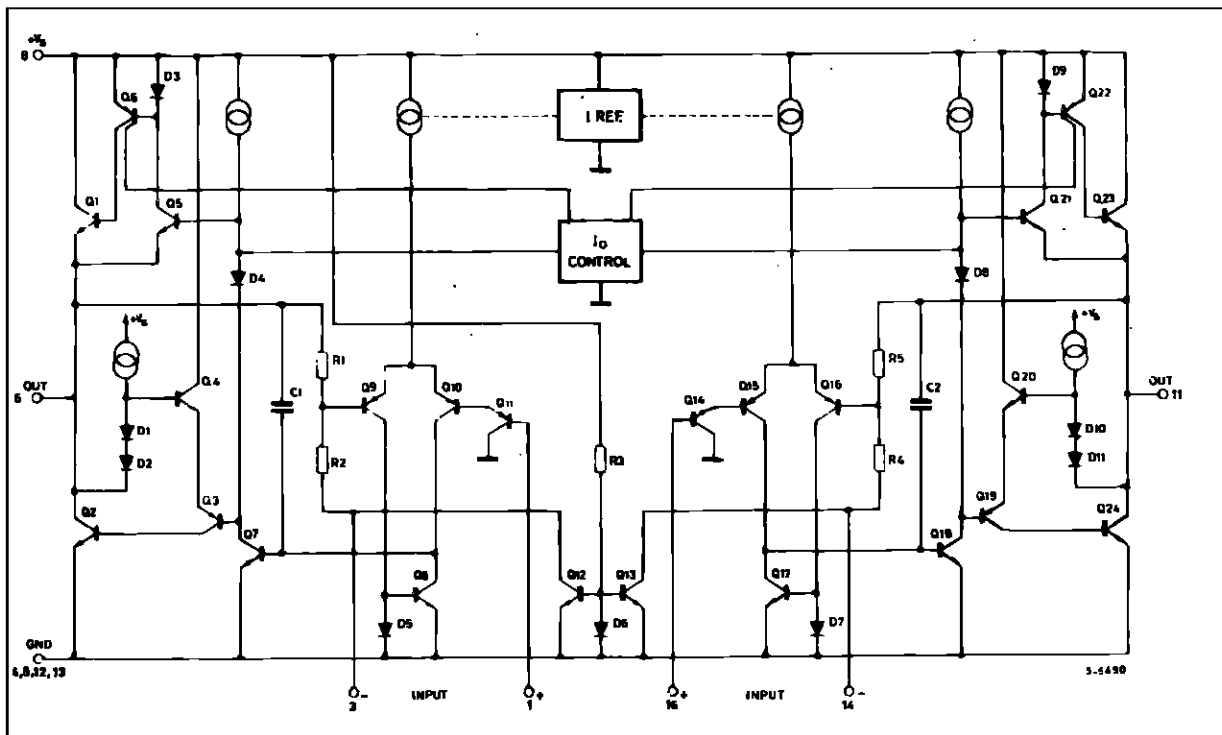


TDA2824

PIN CONNECTION



SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

| Symbol | Parameter | Value | Unit |
|----------------|---|------------|------------------|
| V_S | Supply Voltage | 16 | V |
| I_O | Output Peak Current | 1.5 | A |
| P_{tot} | Total Power Dissipation at $T_{amb} = 50^\circ\text{C}$ $T_{amb} = 70^\circ\text{C}$ | 1.25 4 | W W |
| T_{stg}, T_j | Storage and Junction Temperature | -40 to 150 | $^\circ\text{C}$ |

THERMAL DATA

| Symbol | Parameter | Value | Unit |
|------------------|-------------------------------------|---------|------|
| $R_{th\ j-amb}$ | Thermal Resistance Junction-ambient | Max. 80 | °C/W |
| $R_{th\ j-case}$ | Thermal Resistance Junction-case | Max. 20 | °C/W |

ELECTRICAL CHARACTERISTICS ($V_S = 6V$, $T_{amb} = 25^\circ C$, unless otherwise specified)

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|--------|-----------|-----------------|------|------|------|------|
|--------|-----------|-----------------|------|------|------|------|

STEREO (test circuit of fig. 1)

| | | | | | | |
|-------|-----------------------------|---|-------------|---------------------|----|--------------------|
| V_S | Supply Voltage | | 3 | | 15 | V |
| V_O | Quiescent Output Voltage | $V_S = 9V$ $V_S = 9V$ | | 4 2.7 | | V V |
| I_d | Quiescent Drain Current | | | 6 | 12 | mA |
| I_b | Input Bias Current | | | 100 | | nA |
| P_O | Output Power (each channel) | $d = 10\%$ $f = 1KHz$ $V_S = 9V$ $R_L = 4\Omega$ $V_S = 6V$ $R_L = 4\Omega$ $V_S = 4.5V$ $R_L = 4\Omega$ | 1.3 0.45 | 1.7 0.65 0.32 | | W W W |
| d | Distortion | $V_S = 9V$, $f = 1KHz$ $R_L = 8\Omega$, $P_O = 0.5W$ | | 0.2 | | % |
| G_V | Closed Loop Voltage Gain | $f = 1KHz$ | 36 | 39 | 41 | dB |
| R_i | Input Resistance | $f = 1KHz$ | 100 | | | K Ω |
| e_N | Total Input Noise | $R_S = 10K\Omega$ $B = 22Hz$ to 22KHz Curve A | | 2.5 2 | | μV μV |
| SVR | Supply Voltage Rejection | $f = 100Hz$ | 40 | 50 | | dB |
| CS | Channel Separation | $R_S = 10K\Omega$ $f = 1KHz$ | | 50 | | dB |

BRIDGE (test circuit of fig. 2)

| | | | | | | |
|----------|---------------------------|---|------------|------------------|----|---------------|
| V_S | Supply Voltage | | 3 | | 15 | V |
| V_{OS} | Output Offset Voltage | $R_L = 8\Omega$ | | | 60 | mV |
| I_b | Input Bias Current | | | 100 | | nA |
| P_O | Output Power | $d = 10\%$ $f = 1KHz$ $V_S = 9V$ $R_L = 8\Omega$ $V_S = 6V$ $R_L = 8\Omega$ $V_S = 4.5V$ $R_L = 4\Omega$ | 2.5 0.9 | 3.2 1.35 1 | | W W W |
| d | Distortion ($f = 1KHz$) | $R_L = 8\Omega$ $P_O = 0.5W$ | | 0.2 | | % |
| G_V | Closed Loop Voltage Gain | $f = 1KHz$ | | 39 | | dB |
| e_N | Total Input Noise | $R_S = 10K\Omega$ $B = 22Hz$ to 22KHz Curve A | | 3 2.5 | | mV μV |
| SVR | Supply Voltage Rejection | $f = 100Hz$ | 48 | 60 | | dB |

Figure 1 : Test Circuit (stereo).

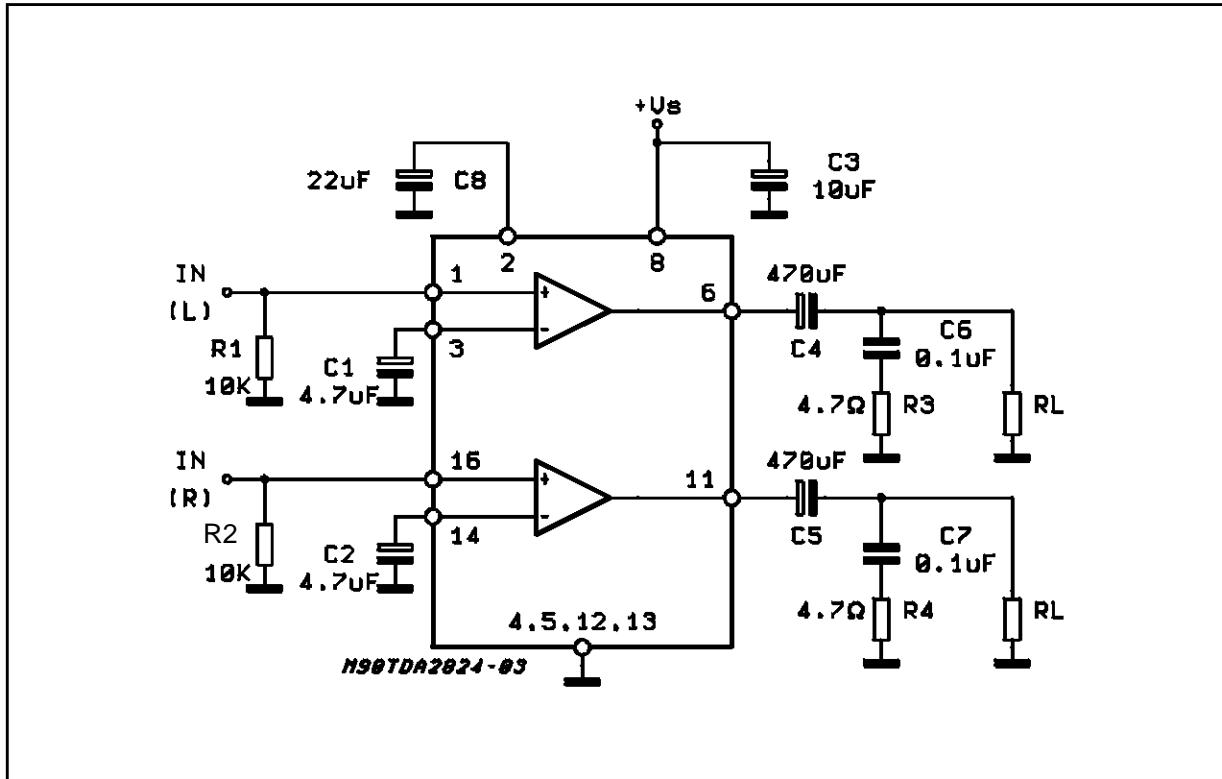


Figure 2: P.C. Board and Component Layout of the Circuit of Figure 1. (1:1 scale)

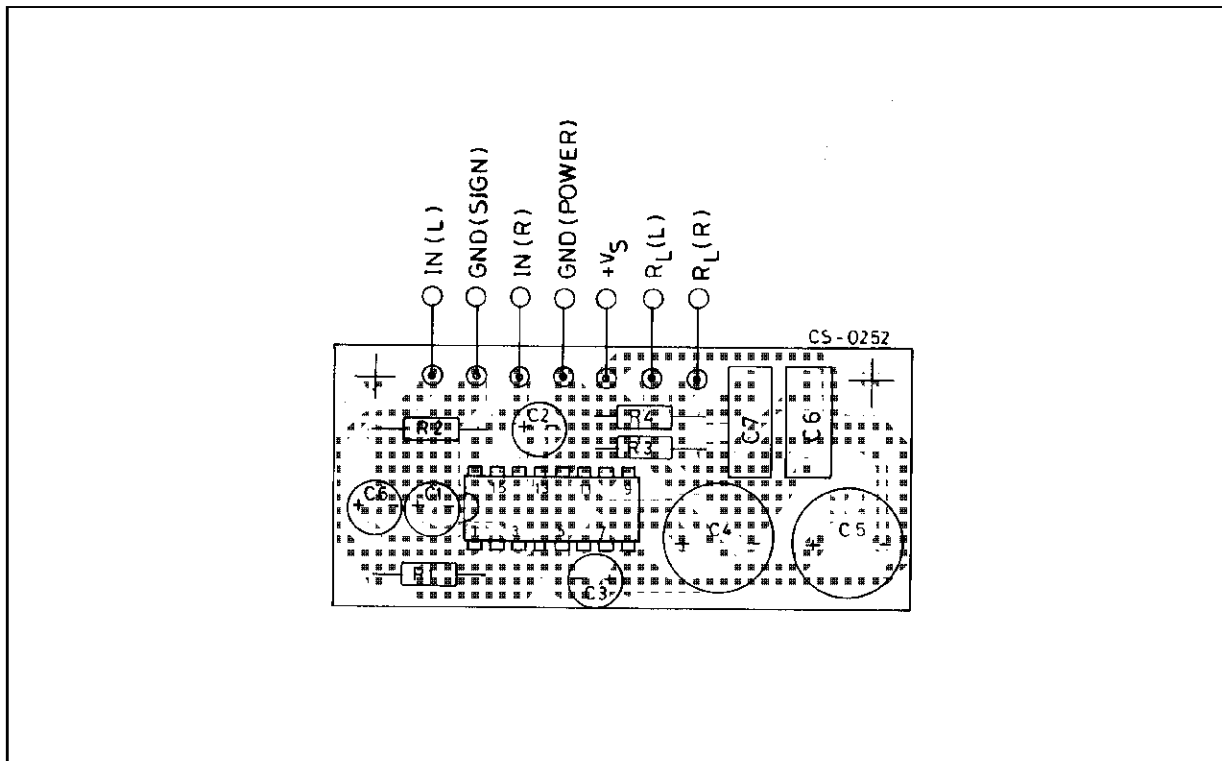


Figure 3 : Test Circuit (bridge).

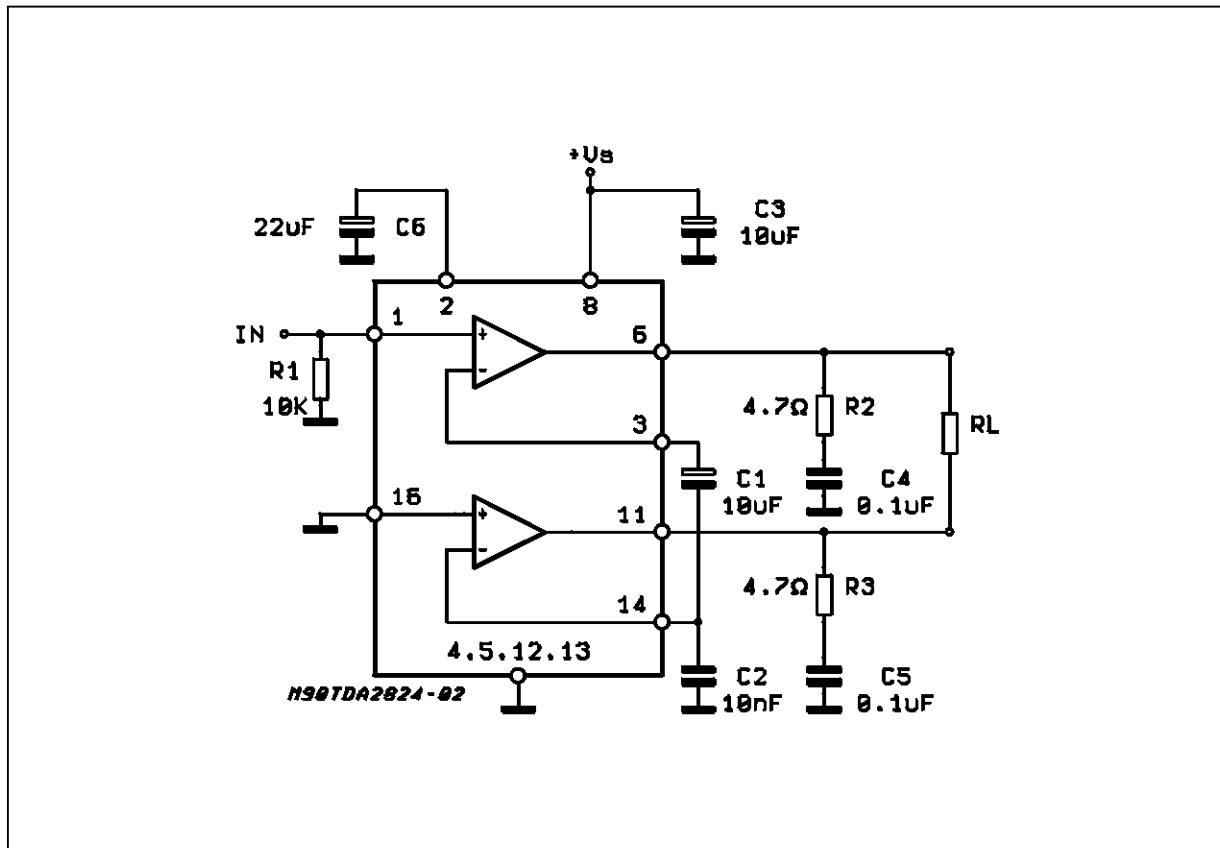


Figure 4: P.C. Board and Component Layout of the Circuit of Figure 3. (1:1 scale)

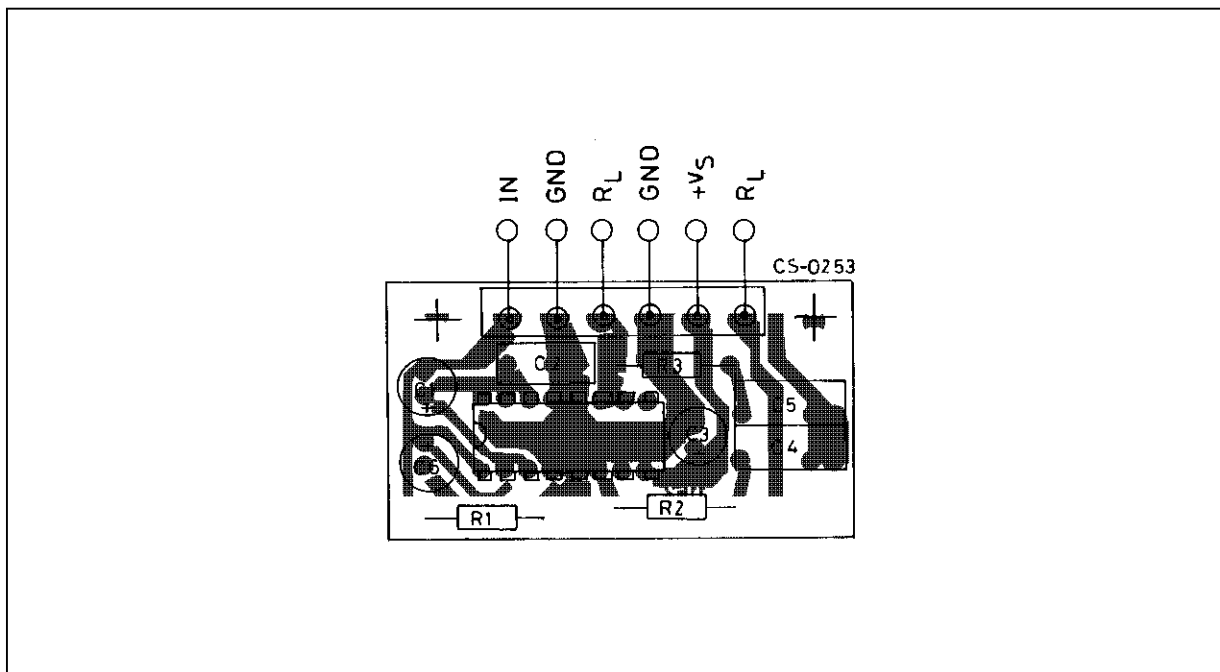


Figure 3 : Output Power vs. Supply Voltage (Stereo).

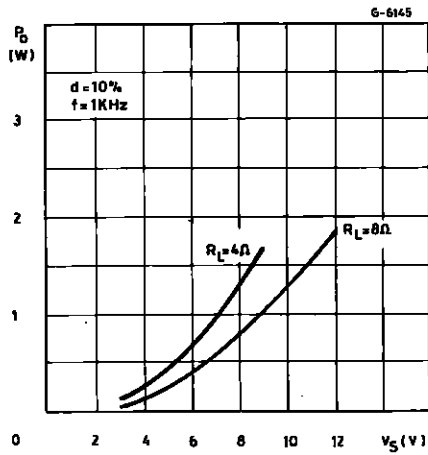


Figure 4 : Output Power vs. Supply Voltage (Bridge).

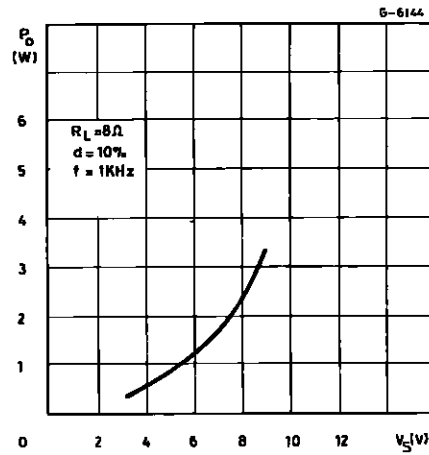


Figure 5 : Distortion vs. Output Power (Bridge).

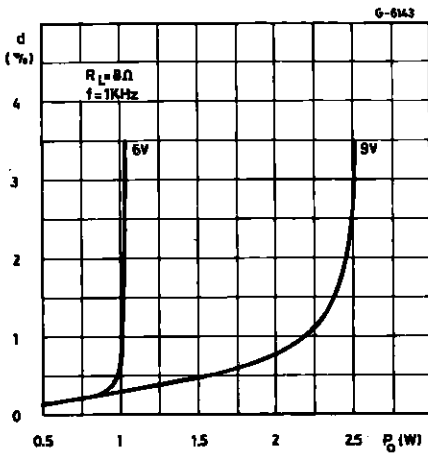


Figure 6 : Distortion vs. Output Power (Bridge).

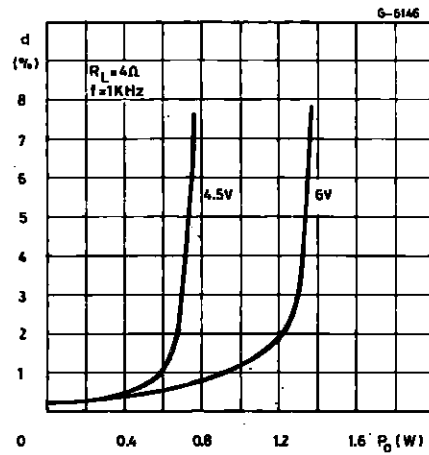


Figure 7 : Supply Voltage Rejection vs. Frequency (Stereo).

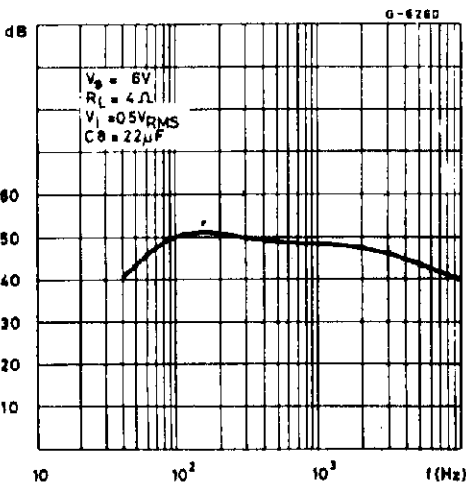


Figure 8 : Quiescent Current vs. Supply Voltage.

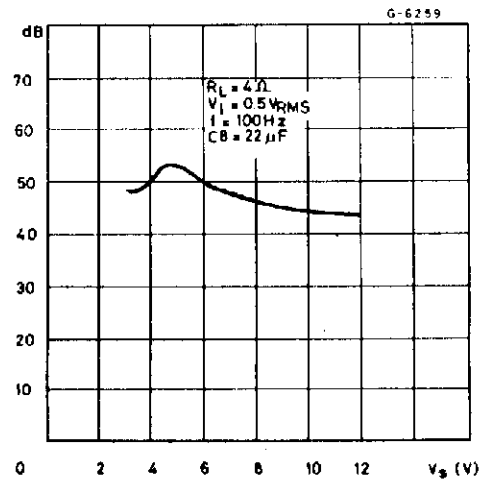


Figure 9 : Quiescent Current vs. Supply Voltage.

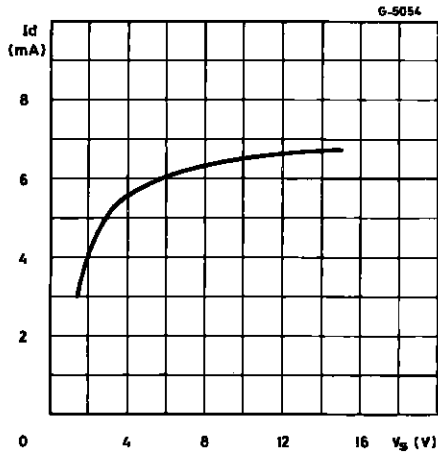


Figure 10 : Total Power Dissipation vs. Output Power (Stereo).

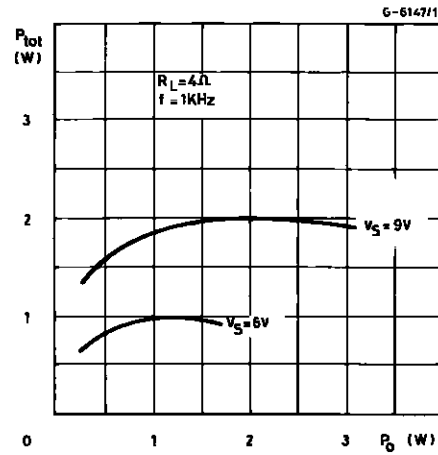


Figure 11 : Total Power Dissipation vs. Output Power (Bridge).

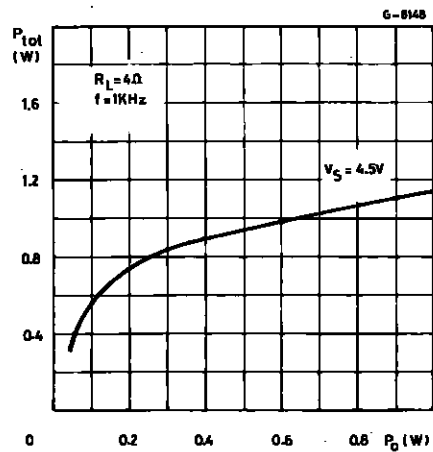
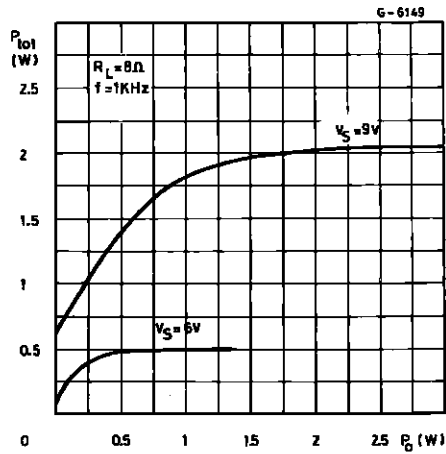


Figure 12 : Total Power Dissipation vs. Output Power (Bridge).

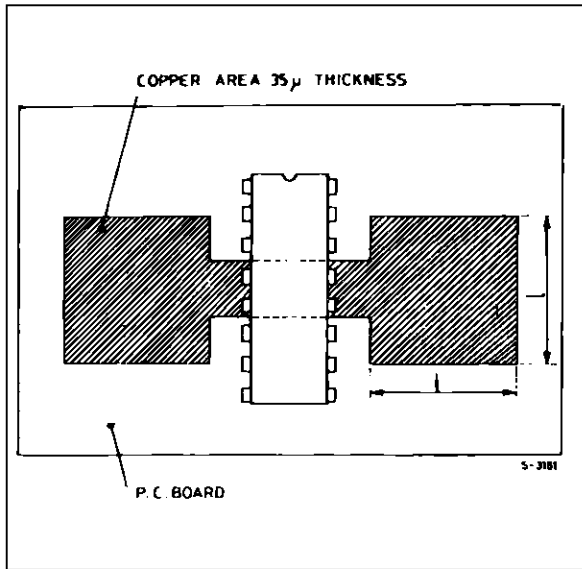


MOUNTING INSTRUCTION

The $R_{thj-amb}$ of the TDA2824 can be reduced by soldering the GND pins to a suitable copper area of the printed circuit board (Figure 13) or to an external heatsink (Figure 14).

The diagram of Figure 15 shows the maximum dissipable power P_{tot} and the $R_{thj-amb}$ as a function of the side "d" of two equal square copper areas having a thickness of $35\ \mu$ (1.4 mils).

Figure 13 : Example of P.C. Board Copper Area which is used as Heatsink.



During soldering the pins temperature must not exceed $260\ ^\circ\text{C}$ and the soldering time must not be longer than 12 seconds.

The external heatsink or printed circuit copper area must be connected to electrical ground.

Figure 14 : External Heatsink Mounting Example.

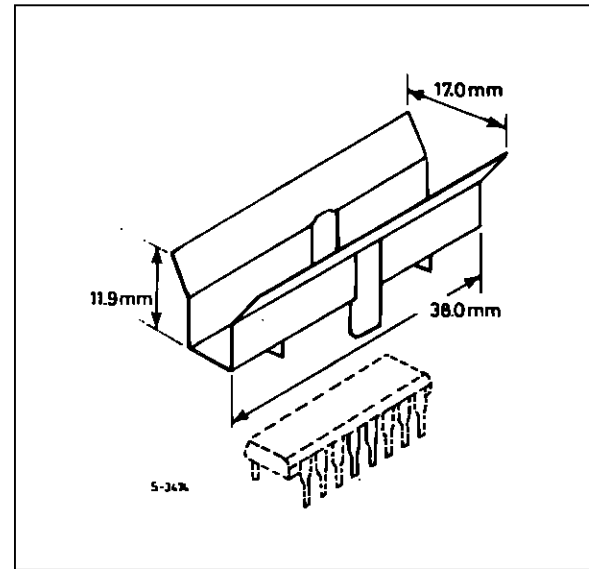


Figure 15 : Maximum Dissipable Power and Junction to Ambient Thermal Resistance vs. Side "d".

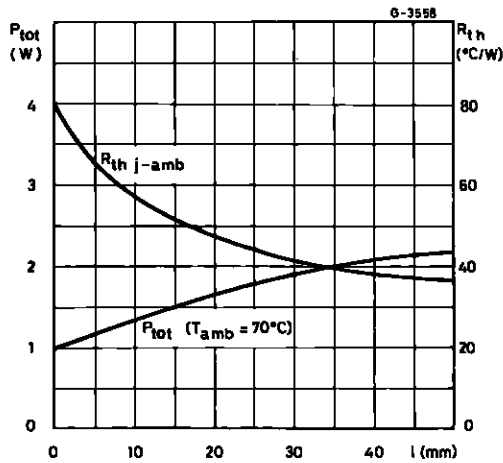
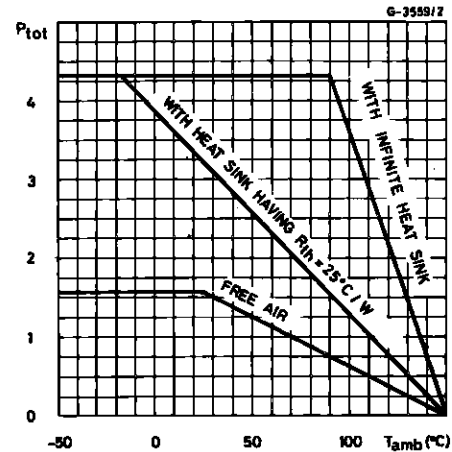
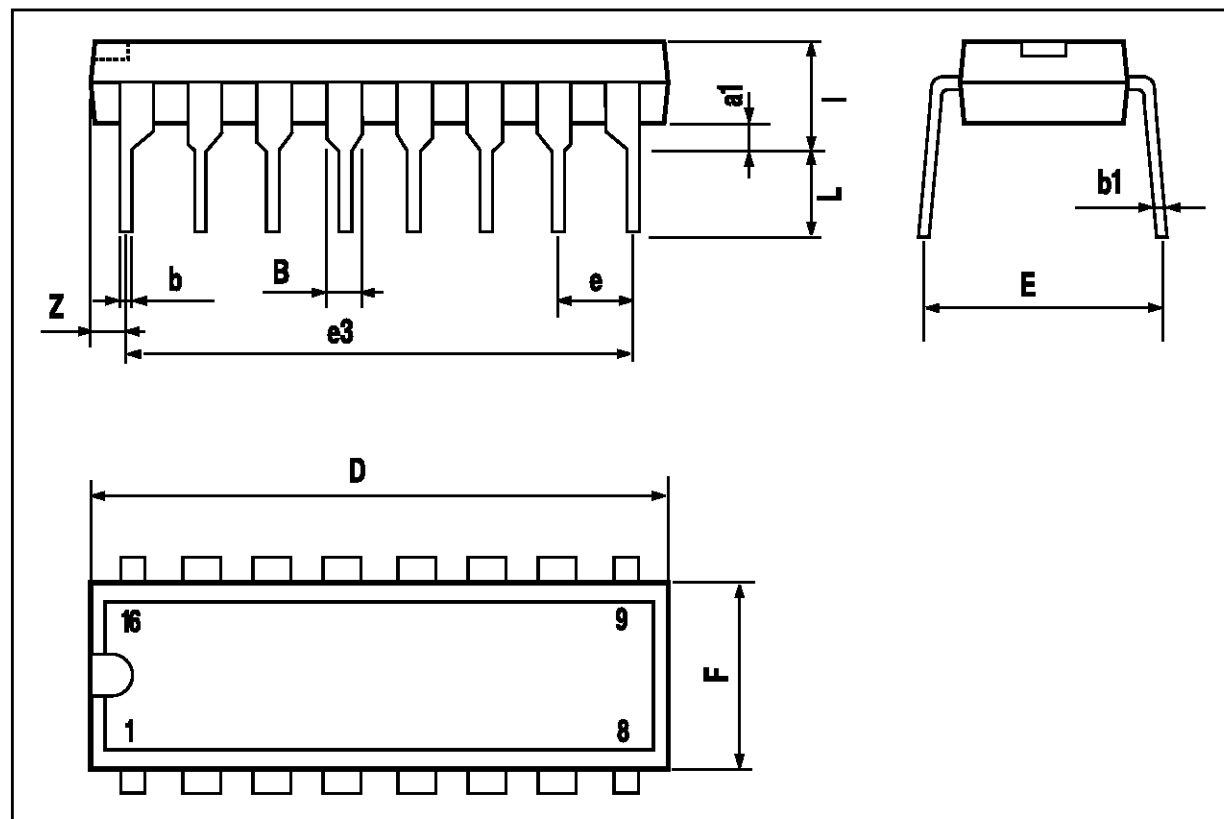


Figure 16 : Maximum Allowable Power Dissipation vs. Ambient Temperature.



POWERDIP 12+2+2 PACKAGE MECHANICAL DATA

| DIM. | mm | | | inch | | |
|------|------|-------|------|-------|-------|-------|
| | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. |
| a1 | 0.51 | | | 0.020 | | |
| B | 0.85 | | 1.40 | 0.033 | | 0.055 |
| b | | 0.50 | | | 0.020 | |
| b1 | 0.38 | | 0.50 | 0.015 | | 0.020 |
| D | | | 20.0 | | | 0.787 |
| E | | 8.80 | | | 0.346 | |
| e | | 2.54 | | | 0.100 | |
| e3 | | 17.78 | | | 0.700 | |
| F | | | 7.10 | | | 0.280 |
| l | | | 5.10 | | | 0.201 |
| L | | 3.30 | | | 0.130 | |
| Z | | | 1.27 | | | 0.050 |



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